★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

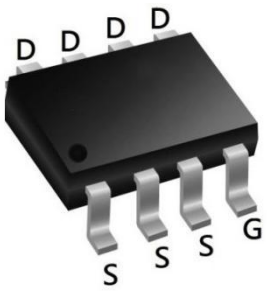
BVDSS	RDSON	ID
-30V	15mΩ	-10.0A

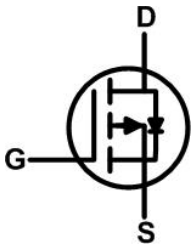
Description

The AO4435 is the high cell density trenched P-ch MOSFETs , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The AO4435 meet the RoHS and Green Product requirement

SOP8 Pin Configuration





Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A= 25℃	-10	A
		T_A= 100℃	-7.0	A
I_{DM}	Pulsed Drain Current note1		-36	A
E_{AS}	Single Pulsed Avalanche Energy note2		25	mJ
P_D	Power Dissipation	T_A= 25℃	3.5	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		48	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D= -250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -30V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance Note3	V_{GS} =-10V, I_D =-9A	-	15	20	mΩ
		V_{GS} =-4.5V, I_D =-5A	-	20	30	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz	-	900	-	pF
C_{oss}	Output Capacitance		-	125	-	pF
C_{rss}	Reverse Transfer Capacitance		-	109	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D = -8A, V_{GS} = -10V	-	42	-	nC
Q_{gs}	Gate-Source Charge		-	8.8	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	7.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = -15V, I_D = -1A, V_{GS}=-10V, R_{GEN}=6Ω	-	13	-	ns
t_r	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	198	-	ns
t_f	Turn-off Fall Time		-	98	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-36	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -9A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃, V_{DD}=-15V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-10A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure1: Output Characteristics

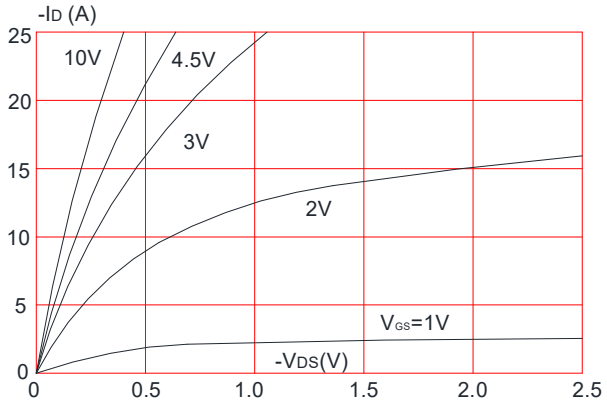


Figure 2: Typical Transfer Characteristics

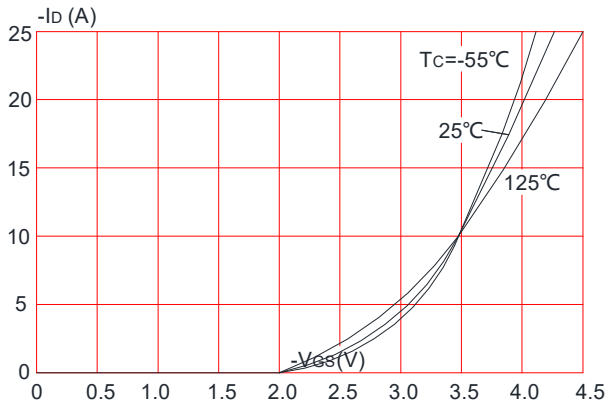


Figure 3: On-resistance vs. Drain Current

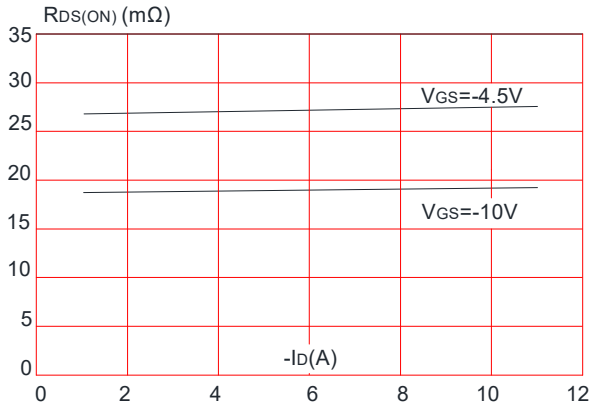


Figure 4: Body Diode Characteristics

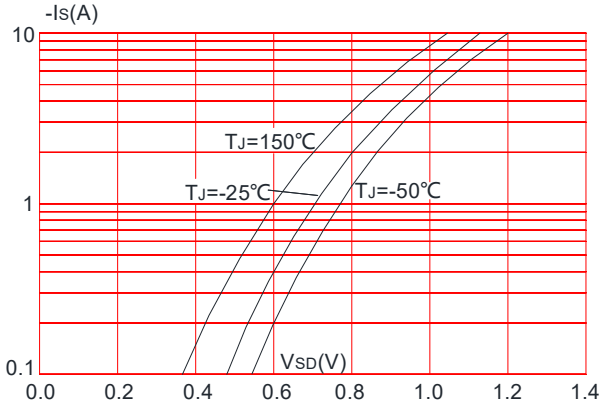


Figure 5: Gate Charge Characteristics

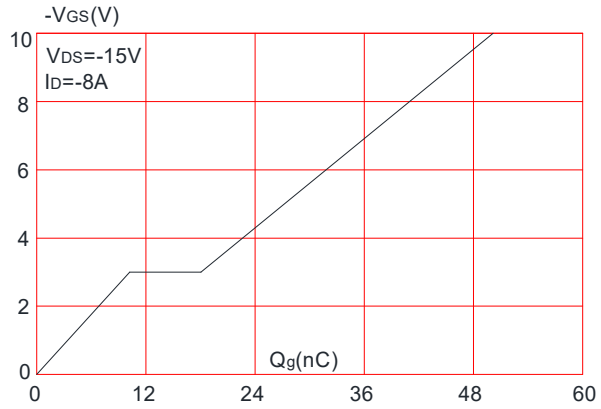


Figure 6: Capacitance Characteristics

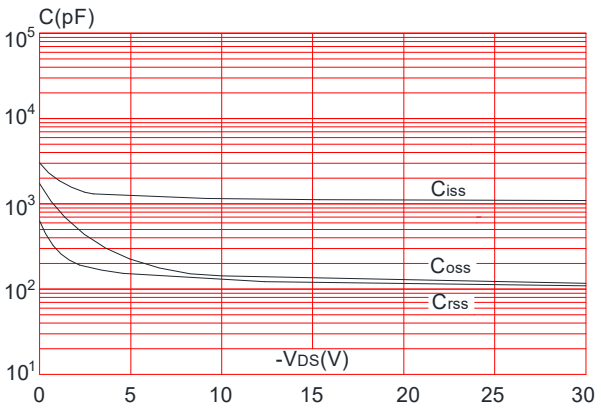


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

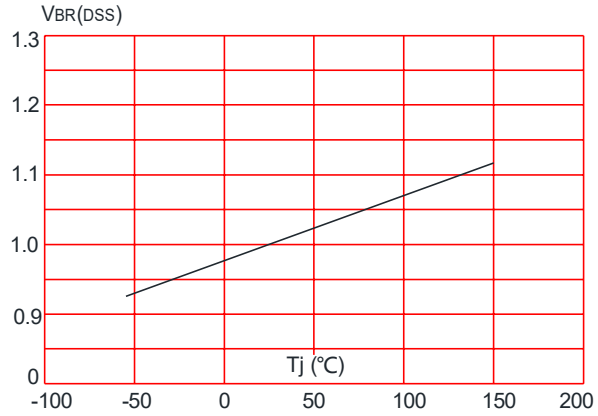


Figure 8: Normalized on Resistance vs. Junction Temperature

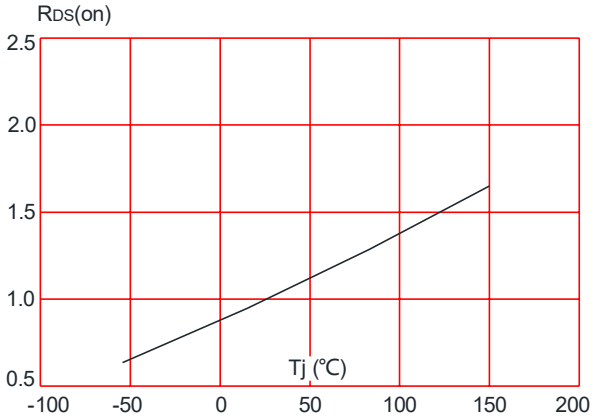


Figure 9: Maximum Safe Operating Area

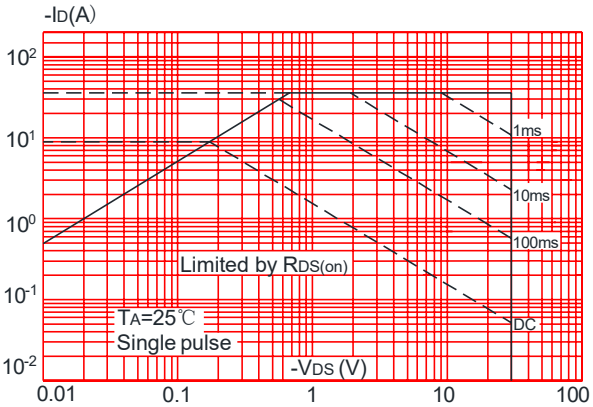


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

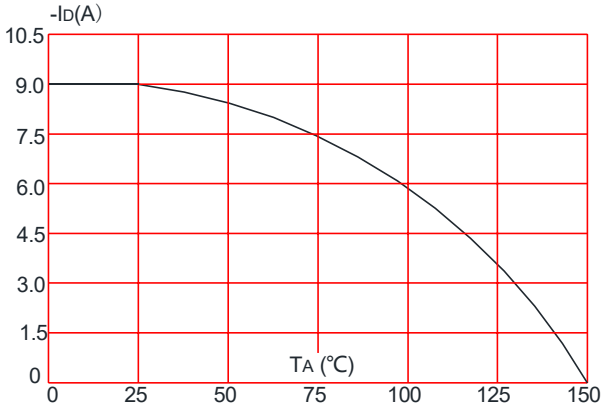
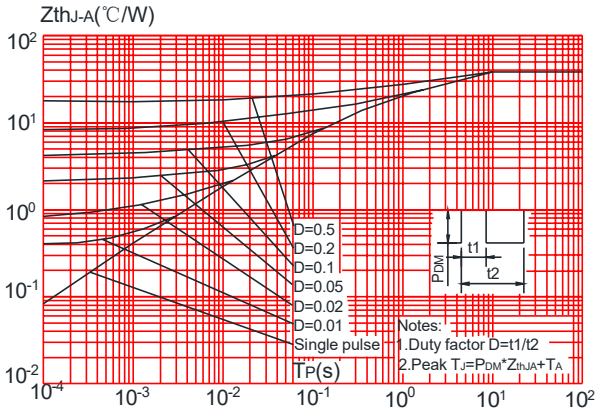


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

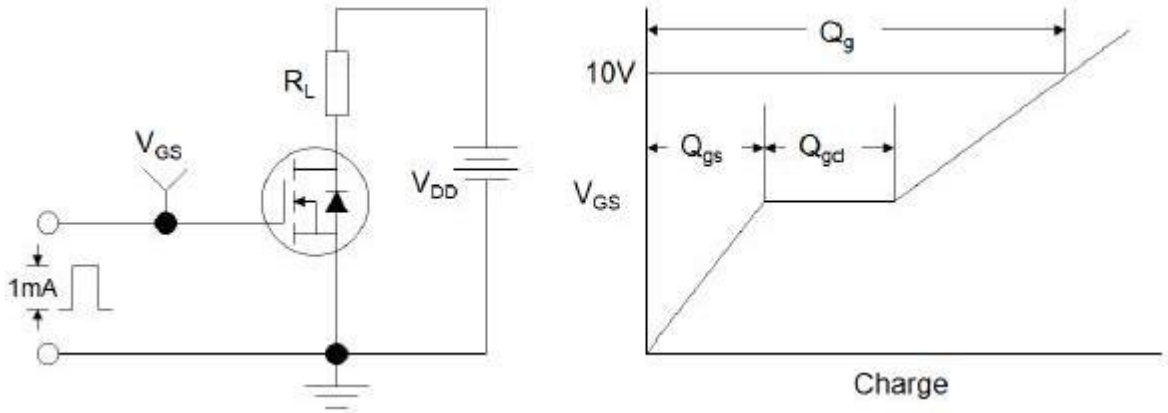


Figure1:Gate Charge Test Circuit & Waveform

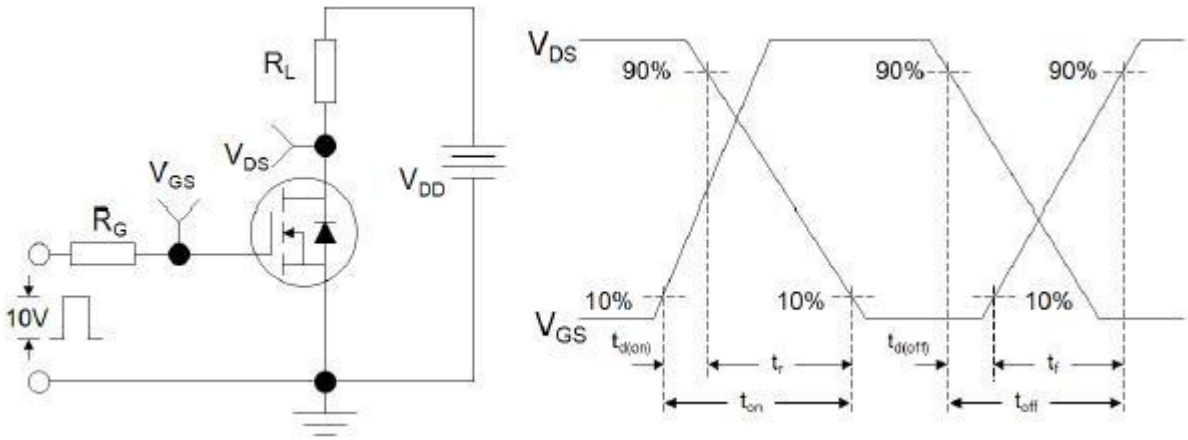


Figure 2: Resistive Switching Test Circuit & Waveforms

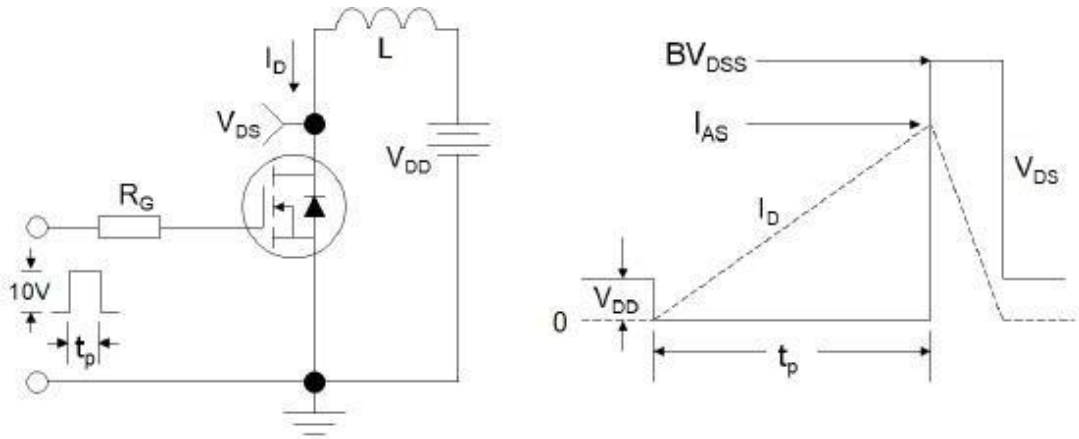
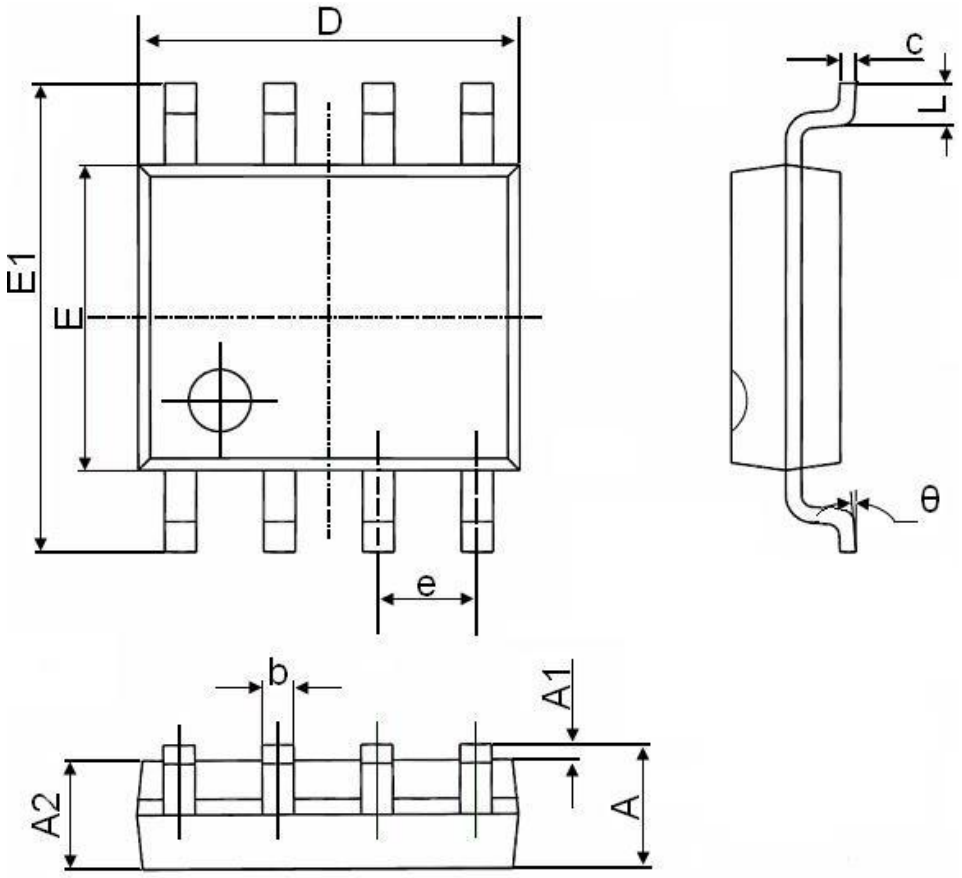


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°